

## Reverse-Conducting IGBT with monolithic body diode

### Features

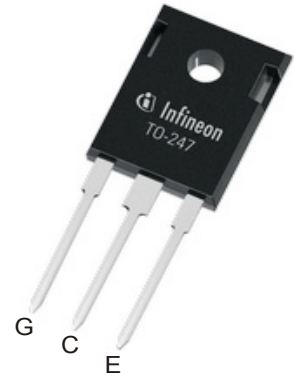
- Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>
- Easy parallel switching capability due to positive temperature coefficient in  $V_{CEsat}$
- High ruggedness and stable temperature behavior
- Low EMI
- Pb-free lead plating; RoHS compliant
- Very low  $V_{CEsat}$  and low  $E_{off}$
- Very tight parameter distribution
- Powerful monolithic reverse-conducting diode with low forward voltage

### Potential applications

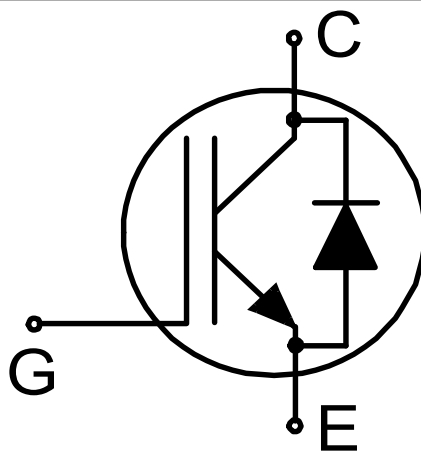
- Induction Cooking
- Microwave Ovens

### Product validation

- Product Validation: Qualified for industrial applications according to the relevant tests of JEDEC47/20/22



### Description



Type	Package	Marking
IHW50N65R6	PG-TO247-3	H50ER6

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1 Package

## 1 Package

**Table 1** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5mm. (0.197in) from case	$L_E$			13.0		nH
Storage temperature	$T_{stg}$		-55		150	°C
Soldering temperature		wave soldering 1.6mm (0.063in.) from case for 10s			260	°C
Mounting torque , M3 screw Maximum of mounting process: 3	$M$				0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W

## 2 IGBT

**Table 2** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Collector-emitter voltage	$V_{CE}$	$T_{vj} \geq 25\text{ °C}$	650	V	
DC collector current, limited by $T_{vjmax}$	$I_C$		$T_C = 25\text{ °C}$	100	A
			$T_C = 100\text{ °C}$	65	
Pulsed collector current, $t_p$ limited by $T_{vjmax}$	$I_{Cpuls}$		150	A	
Turn-off safe operating area		$V_{CE} \leq 650\text{ V}, t_p \leq 1\text{ }\mu\text{s}, T_{vj} \leq 175\text{ °C}$	150	A	
Gate-emitter voltage	$V_{GE}$		$\pm 20$	V	
Transient gate-emitter voltage	$V_{GE}$	$t_p = 10\text{ }\mu\text{s}, D < 0.010$	$\pm 30$	V	
Power dissipation	$P_{tot}$		$T_C = 25\text{ °C}$	251	W
			$T_C = 100\text{ °C}$	125	

**Table 3** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter breakdown voltage	$V_{BRCES}$	$I_C = 0.2\text{ mA}, V_{GE} = 0\text{ V}$	650			V
Collector-emitter saturation voltage	$V_{CE\text{ sat}}$	$I_C = 50.0\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$	1.30	1.60	V
			$T_{vj} = 175\text{ °C}$	1.55		

**Table 3 Characteristic values (continued)**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Gate-emitter threshold voltage	$V_{GEth}$	$I_C = 0.50 \text{ mA}, V_{CE} = V_{GE}$	3.20	4.00	4.80	V
Zero gate voltage collector current	$I_{CES}$	$V_{CE} = 650 \text{ V}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		40	$\mu\text{A}$
			$T_{vj} = 175 \text{ }^\circ\text{C}$		1000	
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0 \text{ V}, V_{GE} = 20 \text{ V}$			100	nA
Transconductance	$g_{fs}$	$I_C = 50.0 \text{ A}, V_{CE} = 20 \text{ V}$		114.0		S
Input capacitance	$C_{ies}$	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 100 \text{ kHz}$		5000		pF
Output capacitance	$C_{oes}$	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 100 \text{ kHz}$		49		pF
Reverse transfer capacitance	$C_{res}$	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 100 \text{ kHz}$		18		pF
Gate charge	$Q_G$	$I_C = 50.0 \text{ A}, V_{GE} = 15 \text{ V}, V_{CE} = 520 \text{ V}$		199		nC
Turn-on delay time	$t_{don}$	$V_{CE} = 400 \text{ V}, V_{GE} = 15 \text{ V},$ $R_{Gon} = 10.0 \text{ } \Omega,$ $R_{Goff} = 10.0 \text{ } \Omega,$ $L_\sigma = 70 \text{ nH}, C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^\circ\text{C},$ $I_C = 50.0 \text{ A}$		21	ns
			$T_{vj} = 175 \text{ }^\circ\text{C},$ $I_C = 50.0 \text{ A}$		21	
Rise time (inductive load)	$t_r$	$V_{CE} = 400 \text{ V}, V_{GE} = 15 \text{ V},$ $R_{Gon} = 10.0 \text{ } \Omega,$ $R_{Goff} = 10.0 \text{ } \Omega,$ $L_\sigma = 70 \text{ nH}, C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^\circ\text{C},$ $I_C = 50.0 \text{ A}$		25	ns
			$T_{vj} = 175 \text{ }^\circ\text{C},$ $I_C = 50.0 \text{ A}$		26	
Turn-off delay time	$t_{doff}$	$V_{CE} = 400 \text{ V}, V_{GE} = 15 \text{ V},$ $R_{Gon} = 10.0 \text{ } \Omega,$ $R_{Goff} = 10.0 \text{ } \Omega,$ $L_\sigma = 70 \text{ nH}, C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^\circ\text{C},$ $I_C = 50.0 \text{ A}$		261	ns
			$T_{vj} = 175 \text{ }^\circ\text{C},$ $I_C = 50.0 \text{ A}$		287	
Fall time (inductive load)	$t_f$	$V_{CE} = 400 \text{ V}, V_{GE} = 15 \text{ V},$ $R_{Gon} = 10.0 \text{ } \Omega,$ $R_{Goff} = 10.0 \text{ } \Omega,$ $L_\sigma = 70 \text{ nH}, C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^\circ\text{C},$ $I_C = 50.0 \text{ A}$		14	ns
			$T_{vj} = 175 \text{ }^\circ\text{C},$ $I_C = 50.0 \text{ A}$		20	
Turn-on energy	$E_{on}$	$V_{CE} = 400 \text{ V}, V_{GE} = 15 \text{ V},$ $R_{Gon} = 10.0 \text{ } \Omega,$ $R_{Goff} = 10.0 \text{ } \Omega,$ $L_\sigma = 70 \text{ nH}, C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^\circ\text{C},$ $I_C = 50.0 \text{ A}$		1.50	mJ
			$T_{vj} = 175 \text{ }^\circ\text{C},$ $I_C = 50.0 \text{ A}$		1.67	
Turn-off energy	$E_{off}$	$V_{CE} = 400 \text{ V}, V_{GE} = 15 \text{ V},$ $R_{Gon} = 10.0 \text{ } \Omega,$ $R_{Goff} = 10.0 \text{ } \Omega,$ $L_\sigma = 70 \text{ nH}, C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^\circ\text{C},$ $I_C = 50.0 \text{ A}$		0.66	mJ
			$T_{vj} = 175 \text{ }^\circ\text{C},$ $I_C = 50.0 \text{ A}$		0.77	

**Table 3** Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Total switching energy	$E_{ts}$	$V_{CE} = 400\text{ V}$ , $V_{GE} = 15\text{ V}$ , $R_{Gon} = 10.0\ \Omega$ , $R_{Goff} = 10.0\ \Omega$ , $L_{\sigma} = 70\text{ nH}$ , $C_{\sigma} = 30\text{ pF}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$ , $I_C = 50.0\text{ A}$		2.16		mJ
			$T_{vj} = 175\text{ }^{\circ}\text{C}$ , $I_C = 50.0\text{ A}$		2.44		
Soft turn-off energy	$E_{off}$	$V_{CE} = 162\text{ V}$ , $V_{GE} = 15\text{ V}$ , $R_{Gon} = 10.0\ \Omega$ , $R_{Goff} = 10.0\ \Omega$ , $C_r = 30\text{ nF}$ , $L_{\sigma} = 70\text{ nH}$ , $C_{\sigma} = 30\text{ pF}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$ , $I_C = 50.0\text{ A}$		0.15		mJ
			$T_{vj} = 175\text{ }^{\circ}\text{C}$ , $I_C = 50.0\text{ A}$		0.30		
IGBT thermal resistance, junction-case	$R_{thjc}$				0.59	K/W	
Operating junction temperature	$T_{vj}$		-40		175	$^{\circ}\text{C}$	

### 3 Diode

**Table 4** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	$V_{RRM}$	$T_{vj} \geq 25\text{ }^{\circ}\text{C}$	650	V	
Diode forward current, limited by $T_{vjmax}$	$I_F$		$T_C = 25\text{ }^{\circ}\text{C}$	39	A
			$T_C = 100\text{ }^{\circ}\text{C}$	24	
Diode pulsed current, limited by $T_{vjmax}$	$I_{Fpuls}$		150	A	
Power dissipation	$P_{tot}$		$T_C = 25\text{ }^{\circ}\text{C}$	59	W
			$T_C = 100\text{ }^{\circ}\text{C}$	29	

**Table 5** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Diode forward voltage	$V_F$	$I_F = 50.0\text{ A}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$	1.51	1.90	V
			$T_{vj} = 175\text{ }^{\circ}\text{C}$		1.67	
Reverse leakage current	$I_R$	$V_R = 650\text{ V}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$		40	$\mu\text{A}$
			$T_{vj} = 175\text{ }^{\circ}\text{C}$		1000	

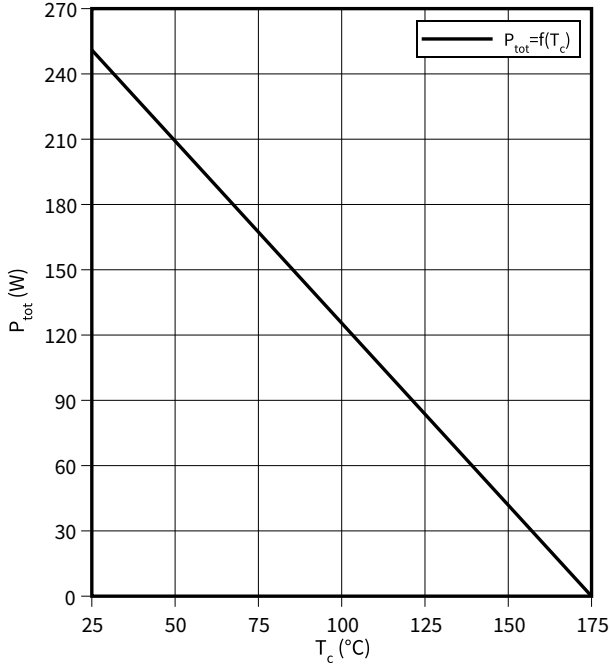
**Table 5** Characteristic values (continued)

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode reverse recovery time	$t_{rr}$	$V_R = 400\text{ V}$	$T_{vj} = 25\text{ °C},$ $I_F = 50.0\text{ A},$ $-di_F/dt = 1000\text{ A}/\mu\text{s}$		108		ns
			$T_{vj} = 175\text{ °C},$ $I_F = 50.0\text{ A},$ $-di_F/dt = 1000\text{ A}/\mu\text{s}$		139		
Diode reverse recovery charge	$Q_{rr}$	$V_R = 400\text{ V}$	$T_{vj} = 25\text{ °C},$ $I_F = 50.0\text{ A},$ $-di_F/dt = 1000\text{ A}/\mu\text{s}$		2.50		$\mu\text{C}$
			$T_{vj} = 175\text{ °C},$ $I_F = 50.0\text{ A},$ $-di_F/dt = 1000\text{ A}/\mu\text{s}$		4.00		
Diode peak reverse recovery current	$I_{rrm}$	$V_R = 400\text{ V}$	$T_{vj} = 25\text{ °C},$ $I_F = 50.0\text{ A},$ $-di_F/dt = 1000\text{ A}/\mu\text{s}$		37.0		A
			$T_{vj} = 175\text{ °C},$ $I_F = 50.0\text{ A},$ $-di_F/dt = 1000\text{ A}/\mu\text{s}$		46.0		
Diode peak rate off fall of reverse recovery current	$di_{rr}/dt$	$V_R = 400\text{ V}$	$T_{vj} = 25\text{ °C},$ $I_F = 50.0\text{ A},$ $-di_F/dt = 1000\text{ A}/\mu\text{s}$		-843		$\text{A}/\mu\text{s}$
			$T_{vj} = 175\text{ °C},$ $I_F = 50.0\text{ A},$ $-di_F/dt = 1000\text{ A}/\mu\text{s}$		-786		
Diode thermal resistance, junction-case	$R_{thjc}$				2.55		K/W
Operating junction temperature	$T_{vj}$			-40		175	$^{\circ}\text{C}$

## 4 Characteristics diagrams

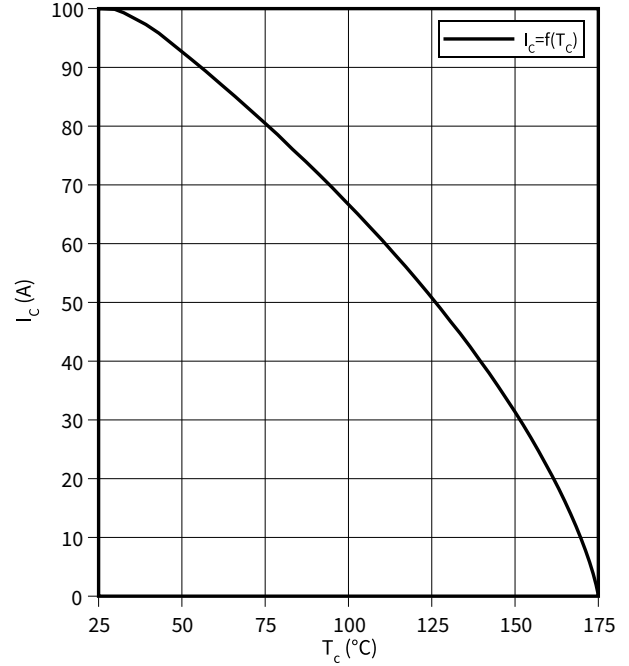
**Power dissipation as a function of case temperature, IGBT**

$P_{tot} = f(T_c)$   
 $T_{vj} \leq 175\text{ }^\circ\text{C}$



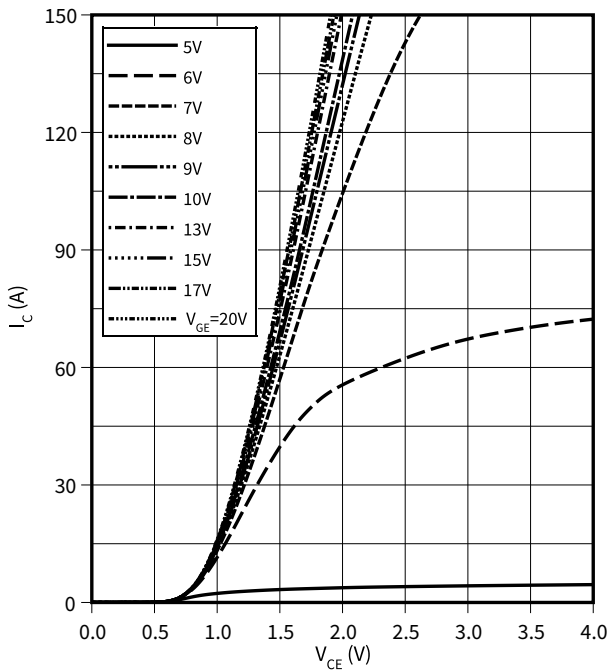
**Collector current as a function of case temperature, IGBT**

$I_C = f(T_c)$   
 $T_{vj} \leq 175\text{ }^\circ\text{C}, V_{GE} = 15\text{ V}$



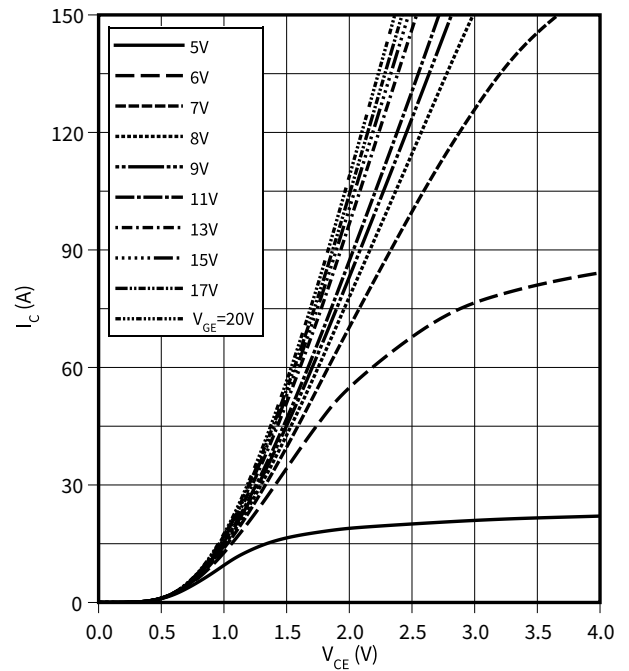
**Typical output characteristic, IGBT**

$I_C = f(V_{CE})$   
 $T_{vj} = 25\text{ }^\circ\text{C}$



**Typical output characteristic, IGBT**

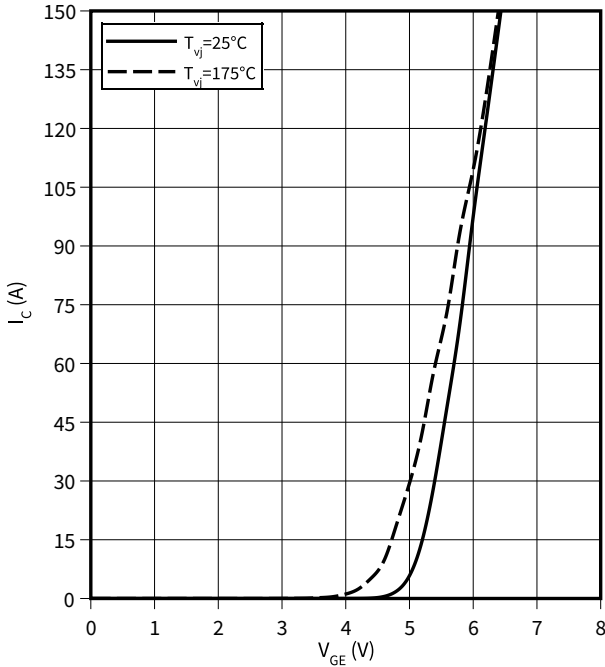
$I_C = f(V_{CE})$   
 $T_{vj} = 175\text{ }^\circ\text{C}$



4 Characteristics diagrams

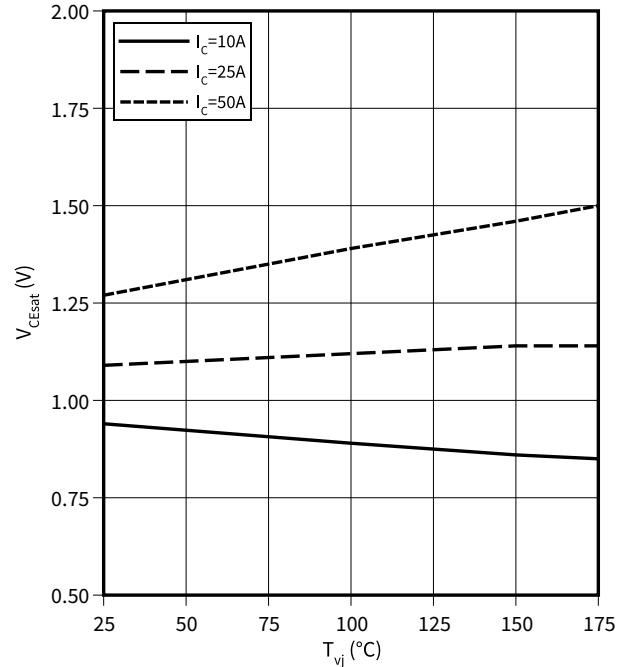
**Typical transfer characteristic, IGBT**

$I_C = f(V_{GE})$   
 $V_{CE} = 20\text{ V}$



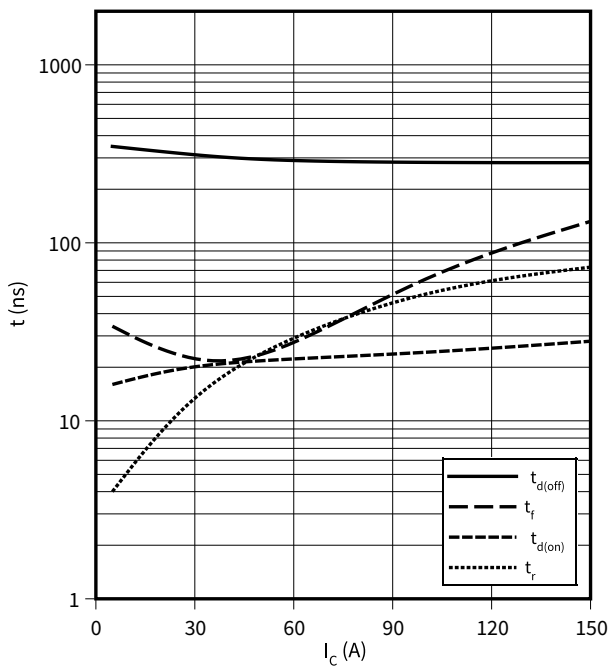
**Typical collector-emitter saturation voltage as a function of junction temperature, IGBT**

$V_{CEsat} = f(T_{vj})$   
 $V_{GE} = 15\text{ V}$



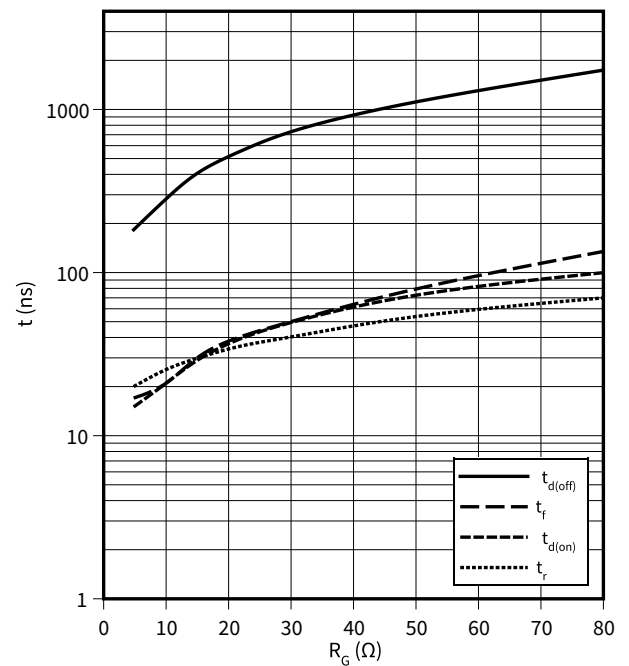
**Typical switching times as a function of collector current, IGBT**

$t = f(I_C)$   
 $R_{Goff} = 10.0\ \Omega$ ,  $V_{CE} = 400\text{ V}$ ,  $T_{vj} = 175^\circ\text{C}$ ,  $V_{GE} = 0/15\text{ V}$ ,  $R_{Gon} = 10.0\ \Omega$



**Typical switching times as a function of gate resistor, IGBT**

$t = f(R_G)$   
 $I_C = 50.0\text{ A}$ ,  $V_{CE} = 400\text{ V}$ ,  $T_{vj} = 175^\circ\text{C}$ ,  $V_{GE} = 0/15\text{ V}$



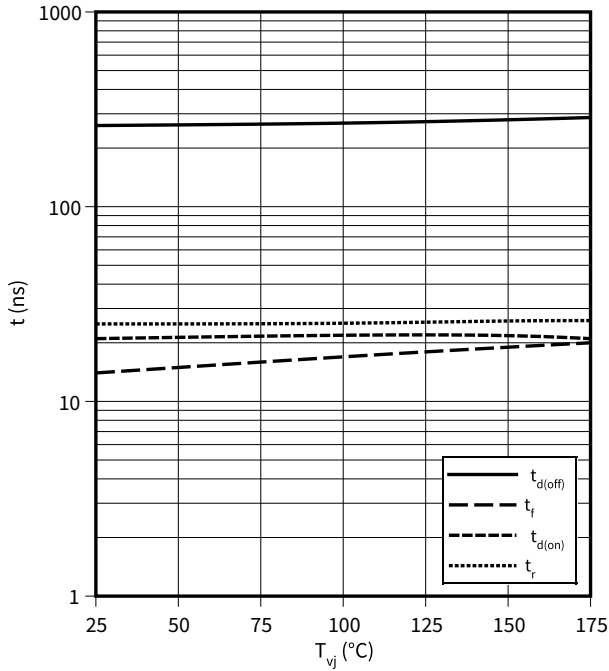


4 Characteristics diagrams

**Typical switching times as a function of junction temperature, IGBT**

$t = f(T_{vj})$

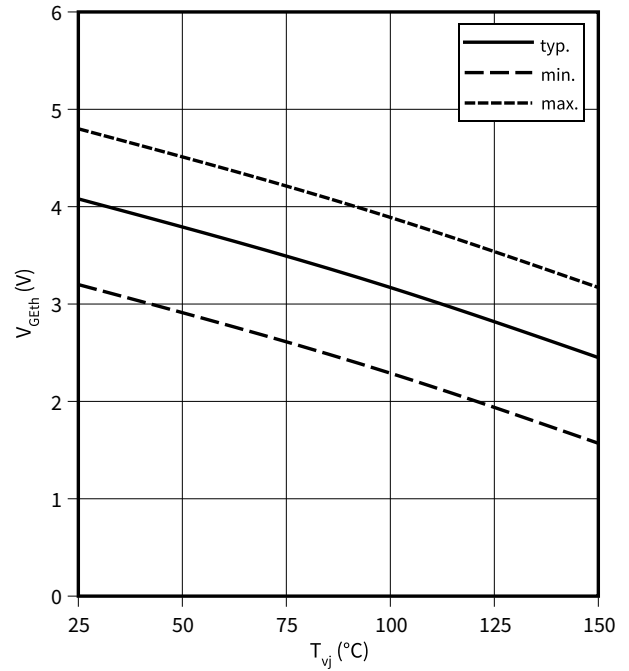
$I_C = 50.0 \text{ A}$ ,  $R_{Goff} = 10.0 \text{ } \Omega$ ,  $V_{CE} = 400 \text{ V}$ ,  $V_{GE} = 0/15 \text{ V}$ ,  $R_{Gon} = 10.0 \text{ } \Omega$



**Gate-emitter threshold voltage as a function of junction temperature, IGBT**

$V_{GEth} = f(T_{vj})$

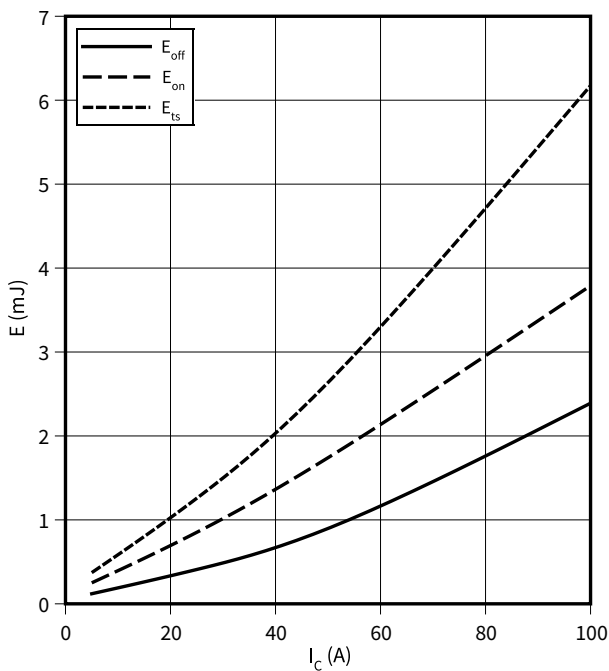
$I_C = 0.50 \text{ mA}$



**Typical switching energy losses as a function of collector current, IGBT**

$E = f(I_C)$

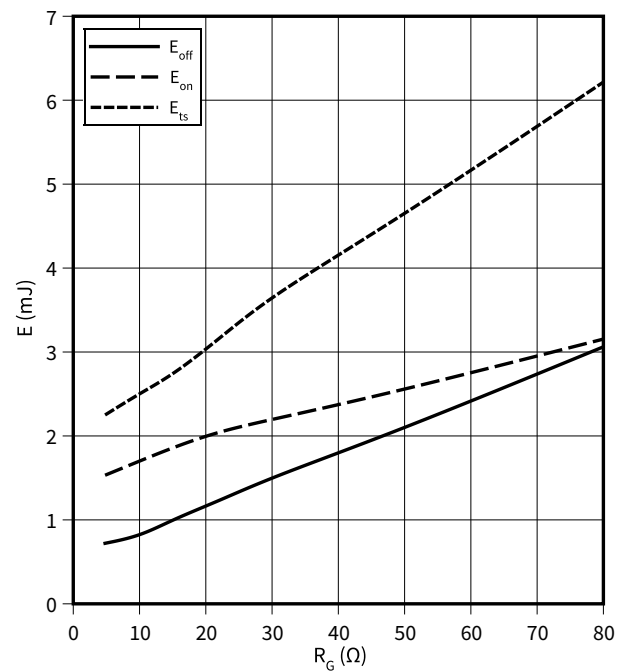
$R_{Goff} = 10.0 \text{ } \Omega$ ,  $V_{CE} = 400 \text{ V}$ ,  $T_{vj} = 175 \text{ } ^\circ\text{C}$ ,  $V_{GE} = 0/15 \text{ V}$ ,  $R_{Gon} = 10.0 \text{ } \Omega$



**Typical switching energy losses as a function of gate resistor, IGBT**

$E = f(R_G)$

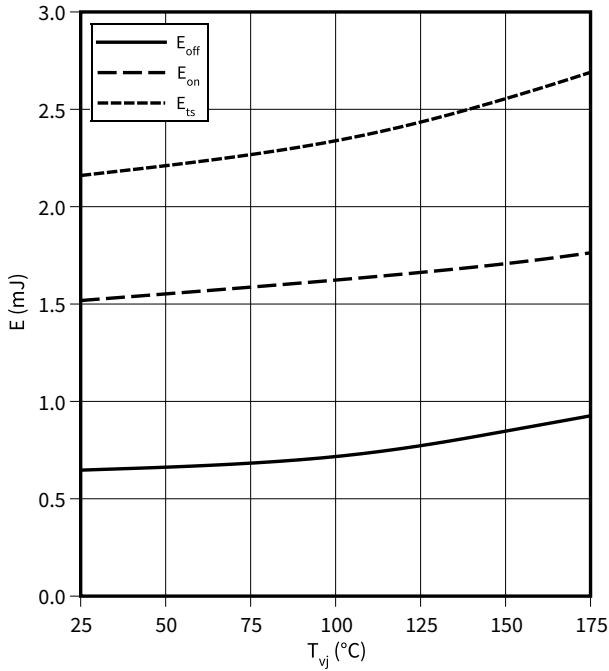
$I_C = 50.0 \text{ A}$ ,  $V_{CE} = 400 \text{ V}$ ,  $T_{vj} = 175 \text{ } ^\circ\text{C}$ ,  $V_{GE} = 0/15 \text{ V}$



4 Characteristics diagrams

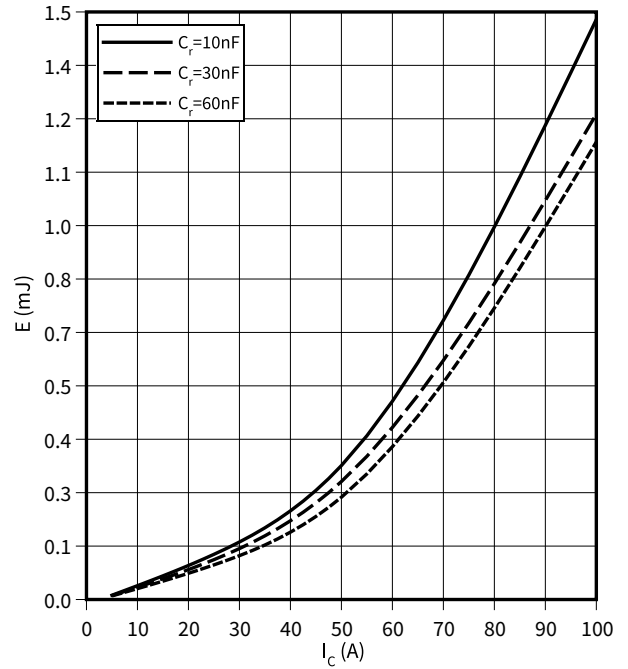
**Typical switching energy losses as a function of junction temperature, IGBT**

$E = f(T_{vj})$   
 $I_C = 50.0 \text{ A}$ ,  $R_{Goff} = 10.0 \text{ } \Omega$ ,  $V_{CE} = 400 \text{ V}$ ,  $V_{GE} = 0/15 \text{ V}$ ,  $R_{Gon} = 10.0 \text{ } \Omega$



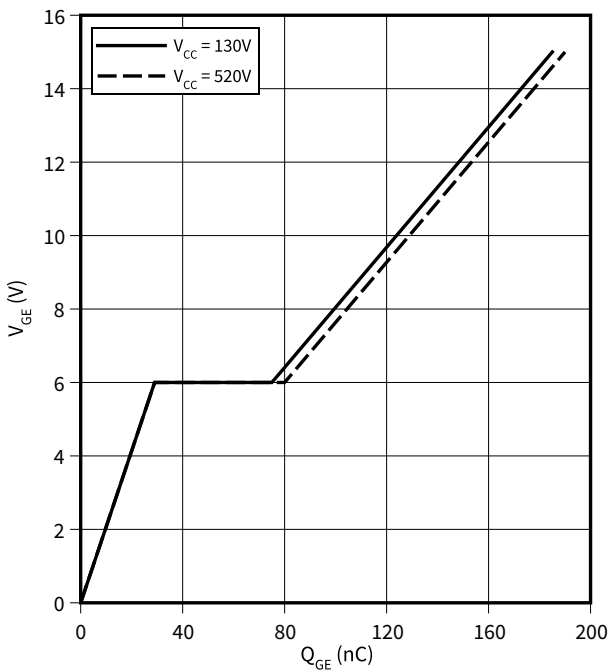
**Typical soft-switching turn-off energy loss as a function of collector current, IGBT**

$E = f(I_C)$   
 $R_{Goff} = 10.0 \text{ } \Omega$ ,  $T_{vj} = 175 \text{ } ^\circ\text{C}$ ,  $V_{GE} = 0/15 \text{ V}$



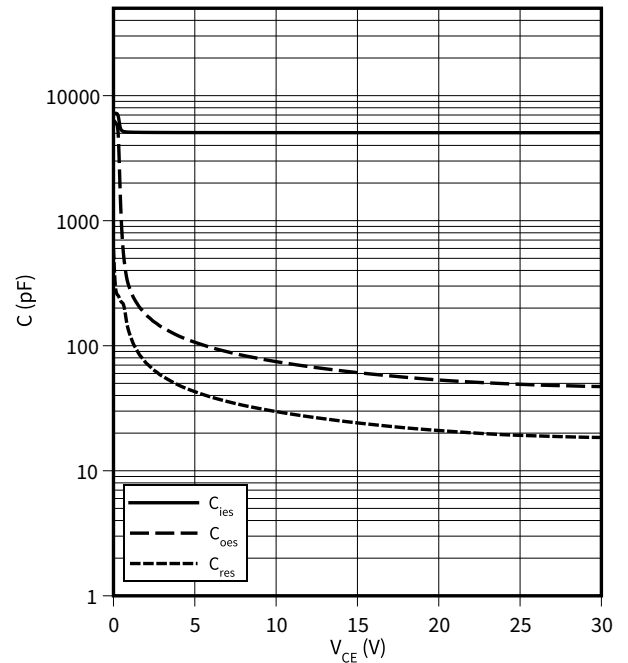
**Typical gate charge, IGBT**

$V_{GE} = f(Q_{GE})$   
 $I_C = 50.0 \text{ A}$



**Typical capacitance as a function of collector-emitter voltage, IGBT**

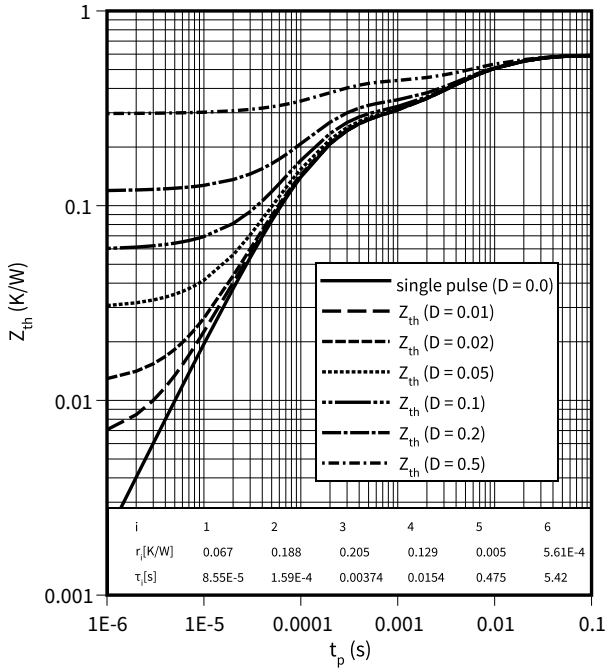
$C = f(V_{CE})$   
 $f = 100 \text{ kHz}$ ,  $V_{GE} = 0 \text{ V}$



4 Characteristics diagrams

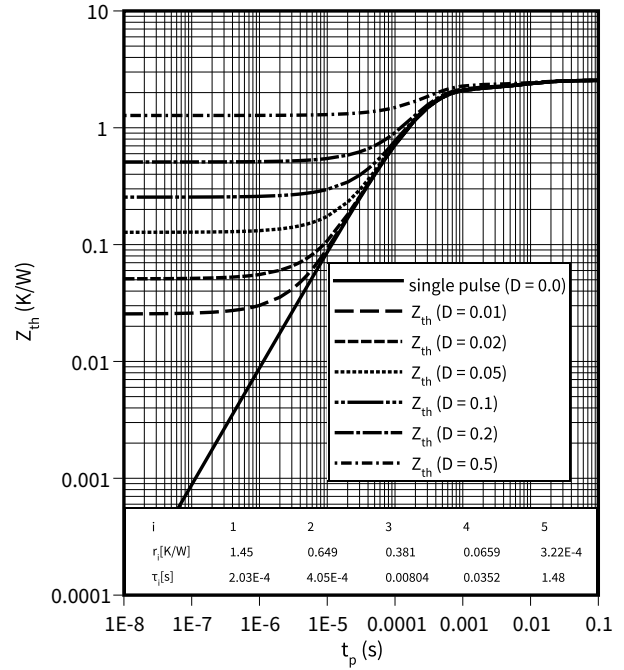
**IGBT transient thermal resistance, IGBT**

$Z_{th} = f(t_p)$   
 $D = t_p/T$



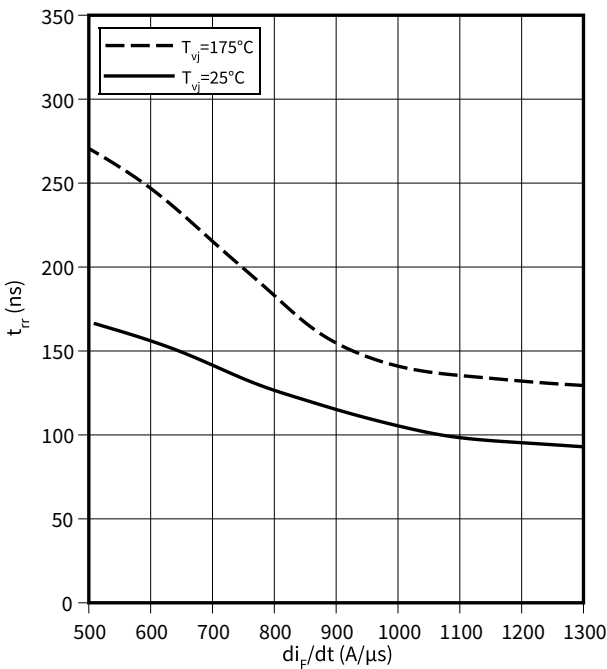
**Diode transient thermal impedance as a function of pulse width, Diode**

$Z_{th} = f(t_p)$   
 $D = t_p/T$



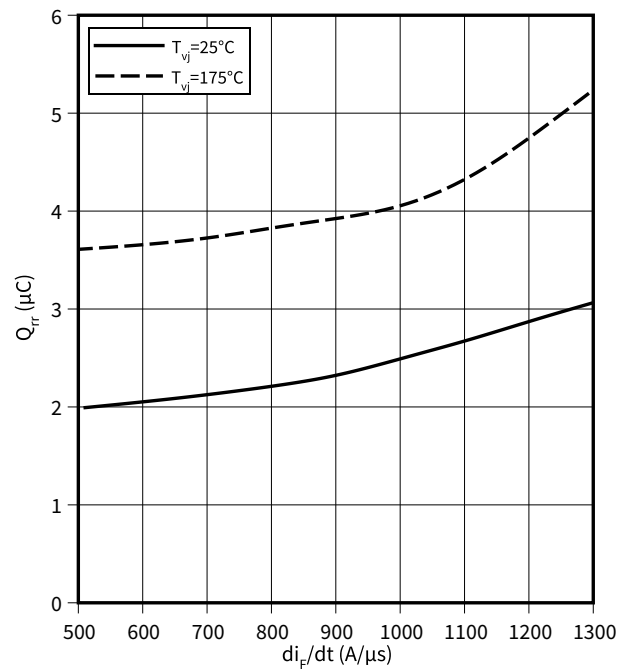
**Typical reverse recovery time as a function of diode current slope, Diode**

$t_{rr} = f(di_F/dt)$   
 $I_F = 50.0 \text{ A}, V_R = 400 \text{ V}$



**Typical reverse recovery charge as a function of diode current slope, Diode**

$Q_{rr} = f(di_F/dt)$   
 $V_R = 400 \text{ V}, I_F = 50.0 \text{ A}$

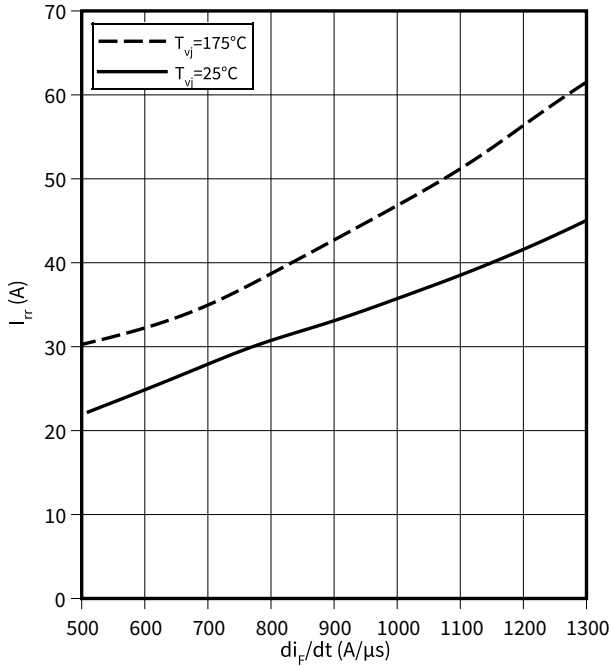


4 Characteristics diagrams

**Typical reverse recovery current as a function of diode current slope, Diode**

$$I_{rr} = f(di_F/dt)$$

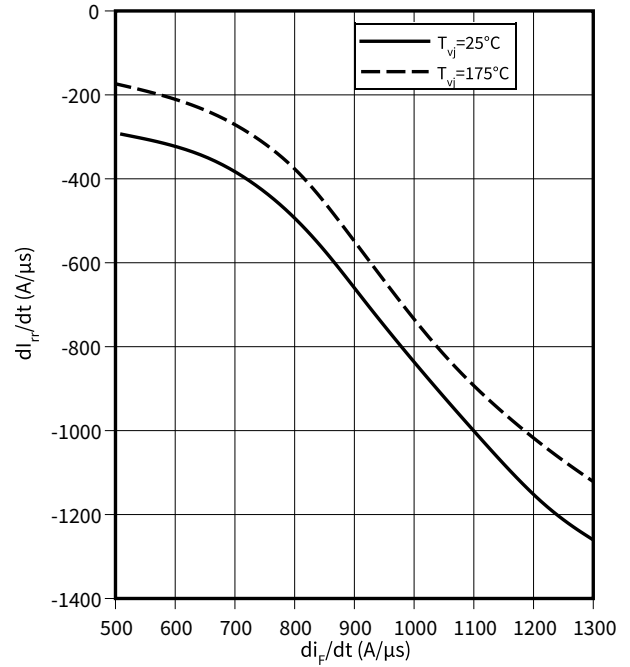
$V_R = 400\text{ V}$ ,  $I_F = 50.0\text{ A}$



**Typical diode peak rate of fall of reverse recovery current as a function of diode current slope, Diode**

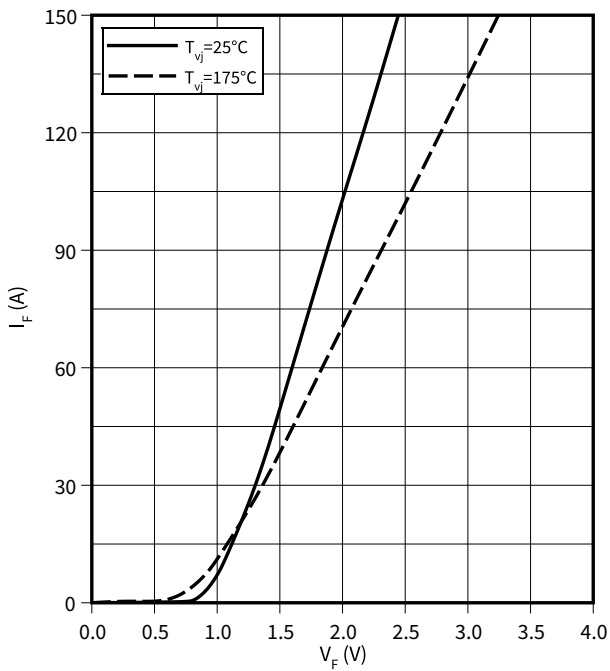
$$dI_{rr}/dt = f(di_F/dt)$$

$V_R = 400\text{ V}$ ,  $I_F = 50.0\text{ A}$



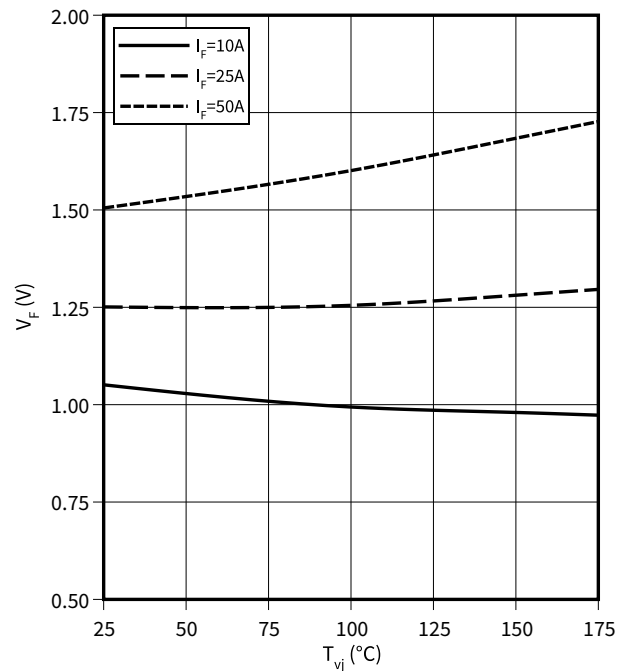
**Typical diode forward current as a function of forward voltage, Diode**

$$I_F = f(V_F)$$



**Typical diode forward voltage as a function of junction temperature, Diode**

$$V_F = f(T_{vj})$$



5 Package outlines

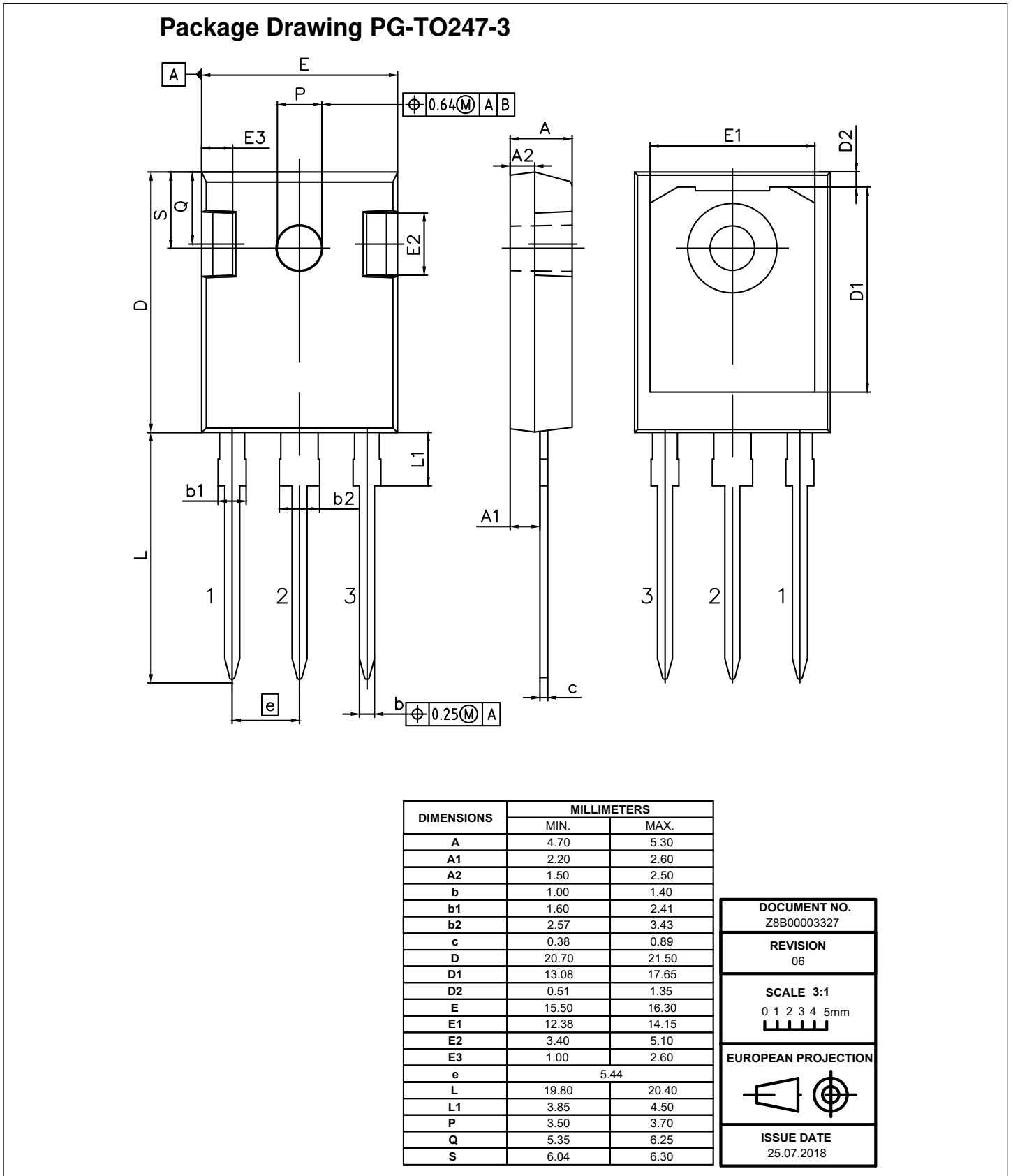


Figure 6

## 6 Testing conditions

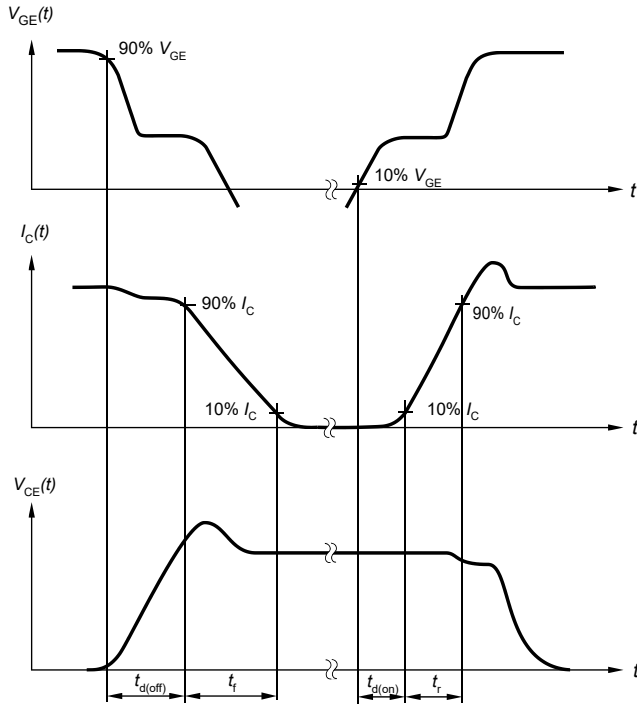


Figure A. Definition of switching times

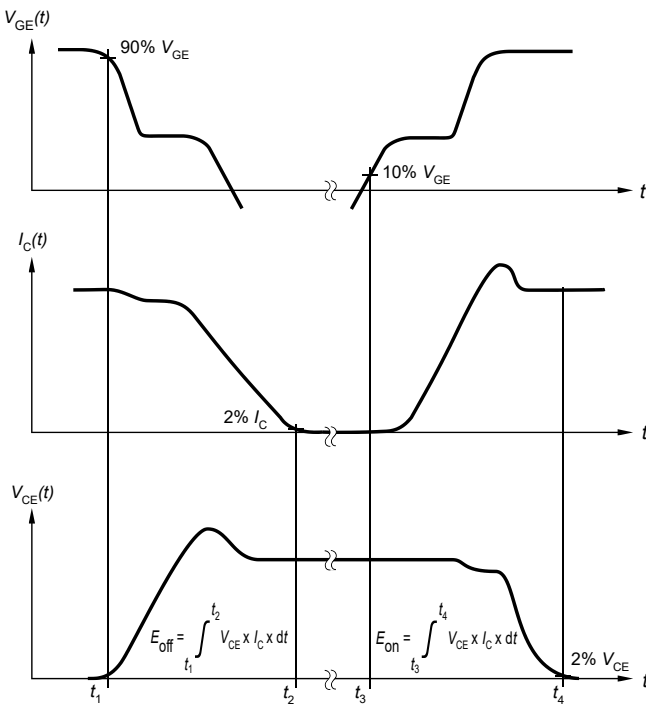


Figure B. Definition of switching losses

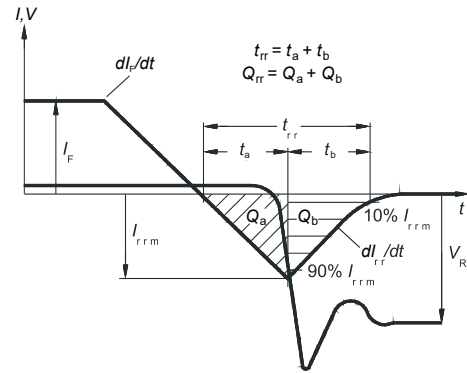


Figure C. Definition of diode switching characteristics

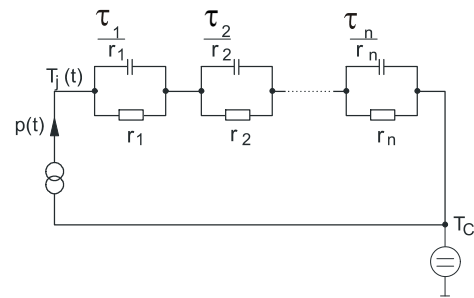


Figure D. Thermal equivalent circuit

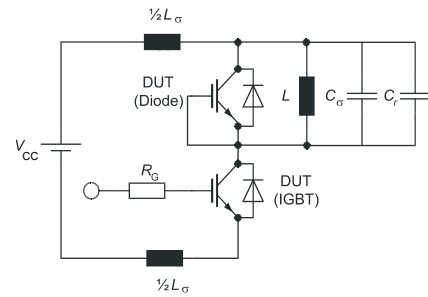


Figure E. Dynamic test circuit  
Parasitic inductance  $L_{\sigma}$ ,  
parasitic capacitor  $C_{\sigma}$ ,  
relief capacitor  $C_r$ ,  
(only for ZVT switching)

Figure 7

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Revision history

## Revision history

Revision	Date of release	Description of changes
1.00	2020.12.21	Final datasheet
1.10	2021.02.22	Soft turn-off energy data changed. Editorial changes in graph.
1.20	2021.03.21	Dynamic characteristic change from 1000 kHz to 100 kHz